

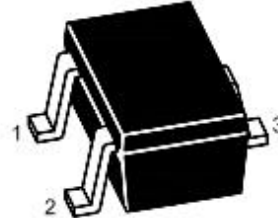
NPN Silicon Epitaxial Planar Transistor

for switching and amplifier applications

FEATURES

- Complementary to MMBT2907AW
- Small Package

MARKING:K3P/1P



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Collector Base Voltage	MMBT2222W MMBT2222AW	V_{CBO}	60 75	V
Collector Emitter Voltage	MMBT2222W MMBT2222AW	V_{CEO}	30 40	V
Emitter Base Voltage	MMBT2222W MMBT2222AW	V_{EBO}	5 6	V
Collector Current		I_C	600	mA
Power Dissipation		P_{tot}	150	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 10\text{ V}$, $I_C = 0.1\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$ at $V_{CE} = 1\text{ V}$, $I_C = 150\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 150\text{ mA}$ at $V_{CE} = 10\text{ V}$, $I_C = 500\text{ mA}$	h_{FE} h_{FE} h_{FE} h_{FE} h_{FE} h_{FE} h_{FE}	35 50 75 50 100 30 40	- - - - 300 - -	- - - - - - -
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$ at $V_{CB} = 60\text{ V}$	I_{CBO}	- -	100 100	nA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60 75	- -	V
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	30 40	- -	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5 6	- -	V
Collector Emitter Saturation Voltage at $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	- - - -	0.4 0.3 1.6 1	V
Base Emitter Saturation Voltage at $I_C = 150\text{ mA}$, $I_B = 15\text{ mA}$ at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{BE(sat)}$	- 0.6 - -	1.3 1.2 2.6 2	V
Transition Frequency at $V_{CE} = 20\text{ V}$, $-I_E = 20\text{ mA}$, $f = 100\text{ MHz}$	f_T	300	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 100\text{ KHz}$	C_{ob}	-	8	pF
Delay Time at $V_{CC} = 30\text{ V}$, $V_{BE(OFF)} = 0.5\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = 15\text{ mA}$	t_d	-	10	ns
Rise Time at $V_{CC} = 30\text{ V}$, $V_{BE(OFF)} = 0.5\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = 15\text{ mA}$	t_r	-	25	ns
Storage Time at $V_{CC} = 30\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = -I_{B2} = 15\text{ mA}$	t_{stg}	-	225	ns
Fall Time at $V_{CC} = 30\text{ V}$, $I_C = 150\text{ mA}$, $I_{B1} = -I_{B2} = 15\text{ mA}$	t_f	-	60	ns

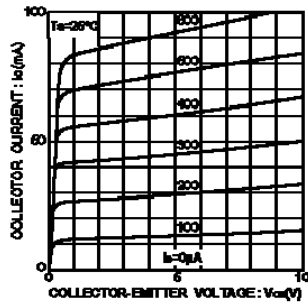


Fig.1 Grounded emitter output characteristics

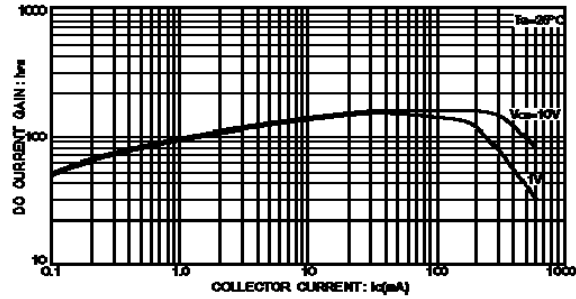


Fig.3 DC current gain vs. collector current (I)

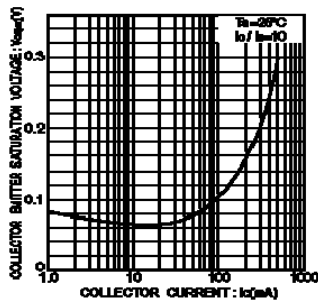


Fig.2 Collector-emitter saturation voltage vs. collector current

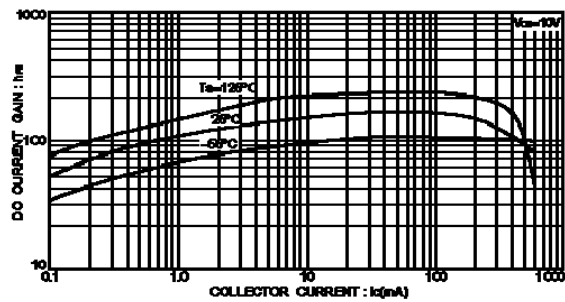


Fig.4 DC current gain vs. collector current (II)

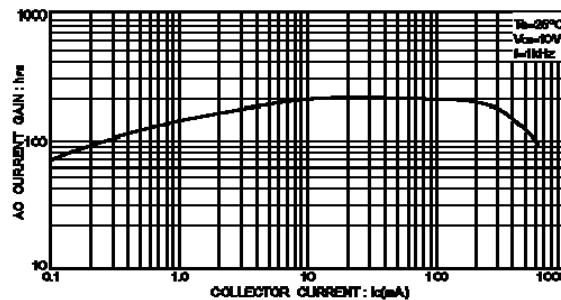


Fig.5 AC current gain vs. collector current

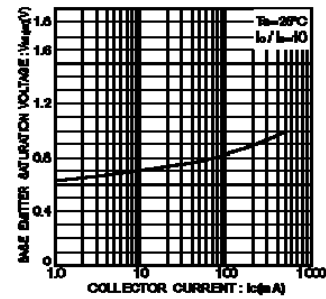
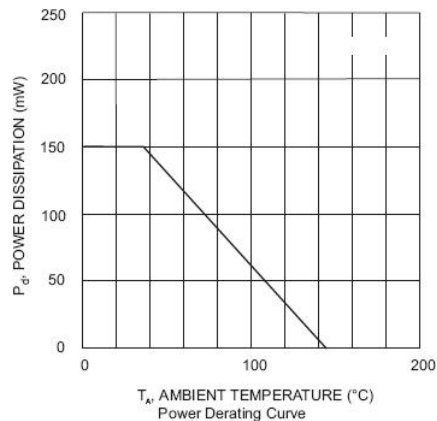
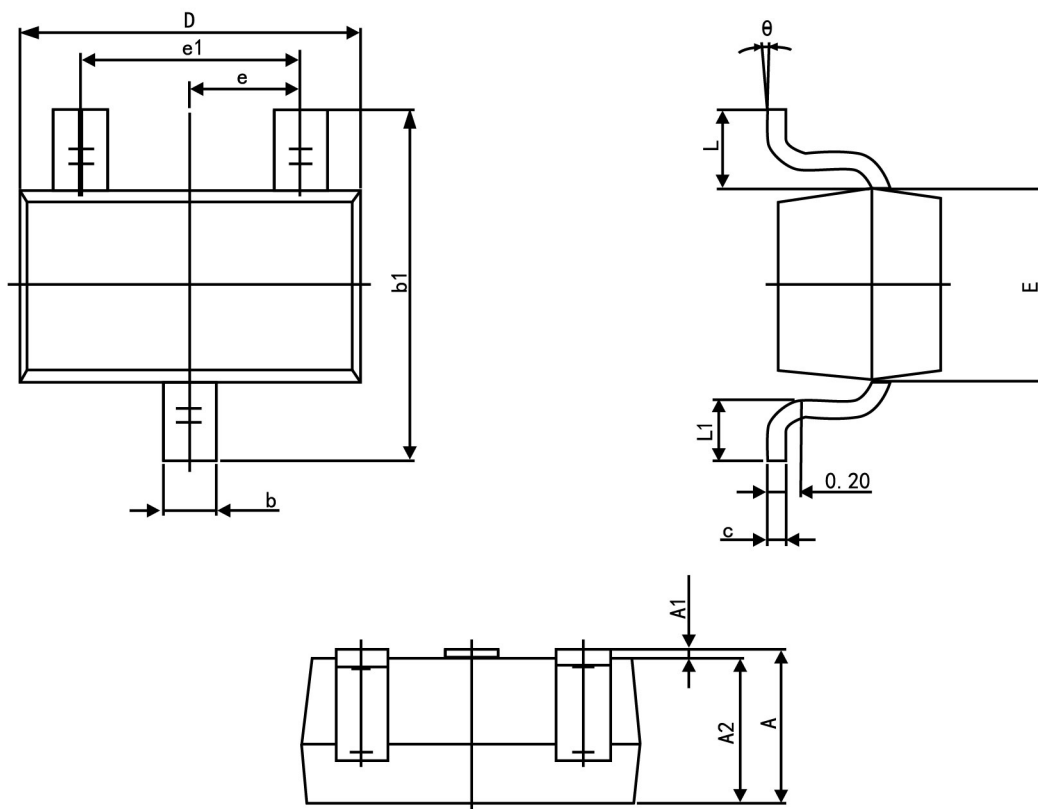


Fig.6 Base-emitter saturation voltage vs. collector current



SOT-323 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	0°	8°